



## UT2300

Preliminary

Power MOSFET

### 20V, 6.0A N-CHANNEL POWER MOSFET

#### DESCRIPTION

The UTC **UT2300** is N-channel enhancement mode Power MOSFET, designed in serried ranks with fast switching speed, low on-resistance and favorable stabilization.

Used in commercial and industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

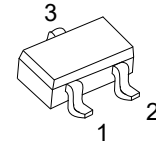
#### FEATURES

\*  $R_{DS(ON)} \leq 30 \text{ m}\Omega$  @  $V_{GS}=10\text{V}$ ,  $I_D=6.0\text{A}$

$R_{DS(ON)} \leq 40 \text{ m}\Omega$  @  $V_{GS}=4.5\text{V}$ ,  $I_D=3.0\text{A}$

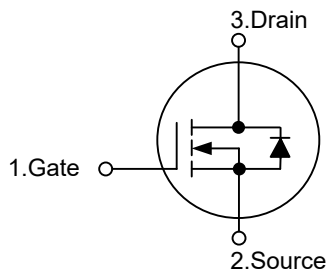
$R_{DS(ON)} \leq 60 \text{ m}\Omega$  @  $V_{GS}=2.5\text{V}$ ,  $I_D=2.0\text{A}$

\* Super High Dense Cell Design for Extremely Low  $R_{DS(ON)}$



SOT-23  
(EIAJ SC-59)

#### SYMBOL



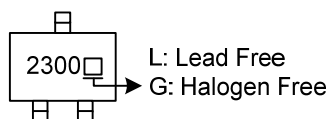
#### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UT2300L-AE3-R	UT2300G-AE3-R	SOT-23	G	S	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<b>UT2300G-AE3-R</b>		(1) Packing Type	(1) R: Tape Reel
		(2) Package Type	(2) AE3: SOT-23
		(3) Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

#### MARKING



■ ABSOLUTE MAXIMUM RATINGS ( $T_c=25^{\circ}\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	20	V
Gate-Source Voltage		$V_{GSS}$	$\pm 12$	V
Drain Current	Continuous	$I_D$	6	A
	Pulsed	$I_{DM}$	20	A
Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	9	mJ
Power Dissipation		$P_D$	0.8	W
Junction Temperature		$T_J$	$-55 \sim +150$	$^{\circ}\text{C}$
Storage Temperature		$T_{STG}$	$-55 \sim +150$	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3.  $L = 0.1\text{mH}$ ,  $I_{AS} = 13.4\text{A}$ ,  $V_{DD} = 15\text{V}$ ,  $R_G = 25\ \Omega$ , Starting  $T_J = 25^{\circ}\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	$\theta_{JA}$	156 (Note)	$^{\circ}\text{C/W}$

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

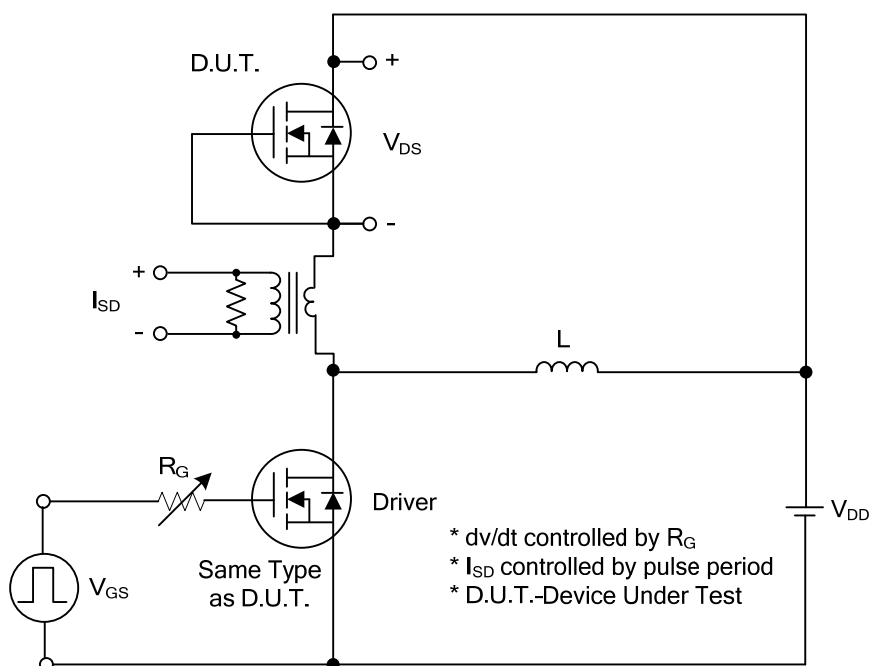
■ ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	20			V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V			100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.4		1.0	V
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =6.0A			30	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3.0A			40	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =2.0A			60	mΩ
DYNAMIC PARAMETERS						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz		305		pF
Output Capacitance	C <sub>OSS</sub>			83		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			70		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q <sub>G</sub>	V <sub>DS</sub> =16V, V <sub>GS</sub> =10V, I <sub>D</sub> =6.0A (Note 1, 2)		16		nC
Gate Source Charge	Q <sub>GS</sub>			1		nC
Gate Drain Charge	Q <sub>GD</sub>			1		nC
Turn-ON Delay Time	t <sub>D(ON)</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =6.0A R <sub>G</sub> =3Ω (Note 1, 2)		4		ns
Turn-ON Rise Time	t <sub>r</sub>			14		ns
Turn-OFF Delay Time	t <sub>D(OFF)</sub>			13		ns
Turn-OFF Fall-Time	t <sub>f</sub>			17		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I <sub>s</sub>				6	A
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	I <sub>s</sub> =1.25A			1.3	V

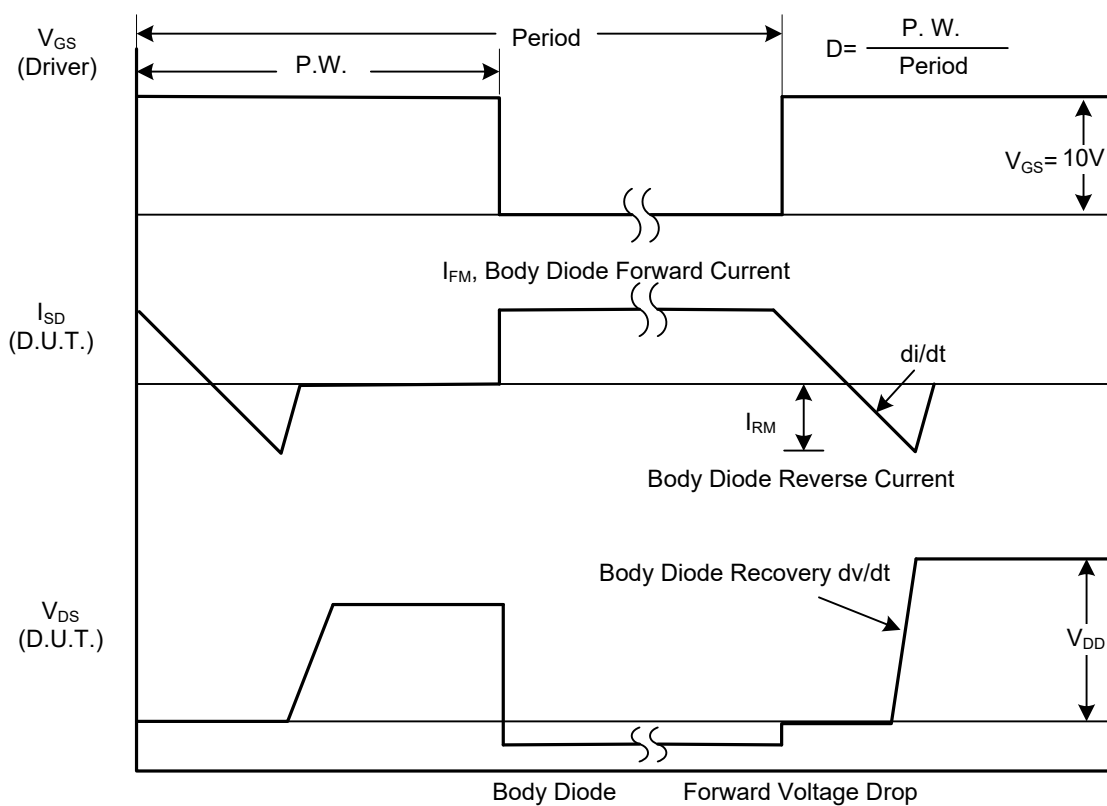
Notes: 1. Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$ .

2. Essentially independent of operating temperature.

# ■ TEST CIRCUITS AND WAVEFORMS

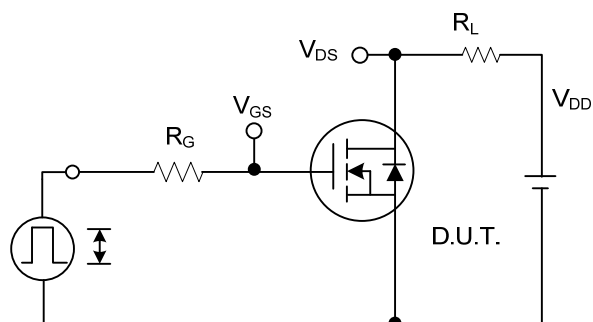


Peak Diode Recovery dv/dt Test Circuit

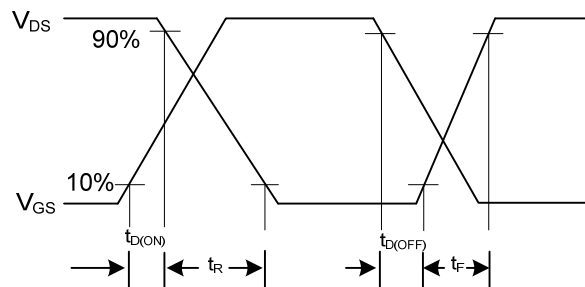


Peak Diode Recovery dv/dt Waveforms

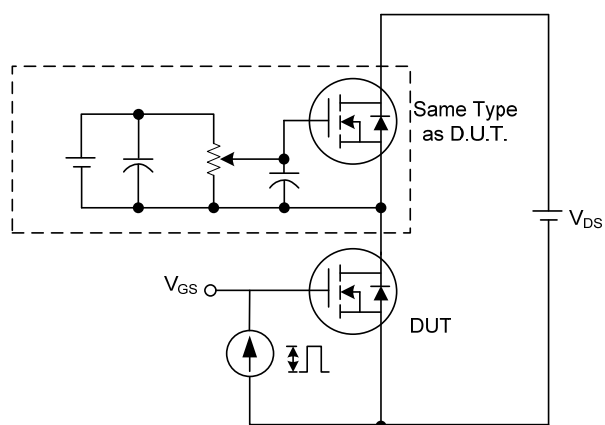
## ■ TEST CIRCUITS AND WAVEFORMS



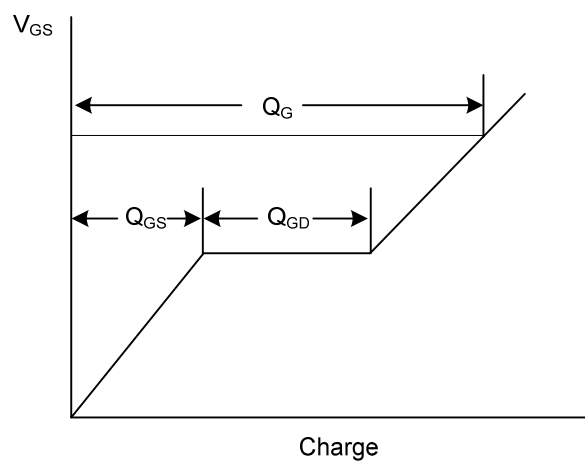
Switching Test Circuit



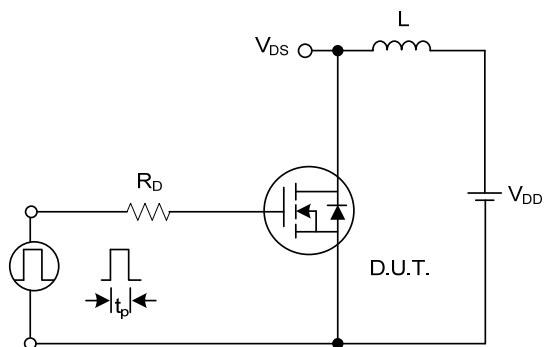
Switching Waveforms



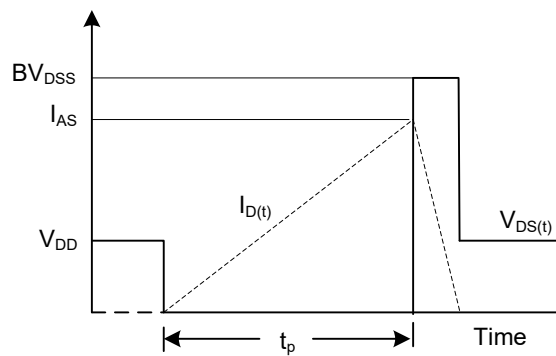
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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